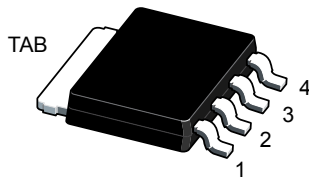
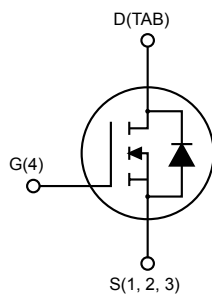


Automotive-grade N-channel 40 V, 1.2 mΩ typ., 100 A STripFET™ F7 Power MOSFET in a LPAK 5x6 package


LPAK 5x6


G4S123DTAB_LPAK



Features

Order code	V _{DS}	R _{DS(on)} max	I _D
STK224N4F7AG	40 V	1.5 mΩ	100 A

- AEC-Q101 qualified 
- Among the lowest R_{DS(on)} on the market
- Excellent FoM (figure of merit)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Product status

STK224N4F7AG

Product summary

Order code	STK224N4F7AG
Marking	224N4F7
Package	LPAK 5x6
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	40	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	100	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	100	A
$I_{DM}^{(2)}$	Drain current (pulsed)	400	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	150	W
I_{AV}	Avalanche current, repetitive or not repetitive (pulse width limited by maximum junction temperature)	56	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AV}$, $V_{DD} = 25\text{ V}$)	470	mJ
T_J	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature range		

1. Drain current is limited by package, the current capability of the silicon is 224 A at 25 $^\circ\text{C}$.

2. Pulse width limited by safe operating area

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb.	31.3	$^\circ\text{C/W}$
$R_{thj-case}$	Thermal resistance junction-case.	1.0	$^\circ\text{C/W}$

1. When mounted on FR-4 board of 1 inch², 2oz Cu, $t < 10\text{ s}$.

2 Electrical characteristics

($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 3. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	40			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 40\text{ V}$			1	μA
I_{GSS}	Gate-body leakage current	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 50\text{ A}$		1.2	1.5	m Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	4060	-	pF
C_{oss}	Output capacitance		-	1100	-	pF
C_{rss}	Reverse transfer capacitance		-	300	-	pF
Q_g	Total gate charge	$V_{DD} = 20\text{ V}$, $I_D = 100\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 13. Test circuit for gate charge behavior)	-	50	-	nC
Q_{gs}	Gate-source charge		-	23	-	nC
Q_{gd}	Gate-drain charge		-	9.8	-	nC

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 20\text{ V}$, $I_D = 50\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	25	-	ns
t_r	Rise time		-	20	-	ns
$t_{d(off)}$	Turn-off delay time		-	48	-	ns
t_f	Fall time		-	31	-	ns

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 100\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.1	V
t_{rr}	Reverse recovery time	$I_D = 100\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$ (see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	41		ns
Q_{rr}	Reverse recovery charge		-	32		nC
I_{RRM}	Reverse recovery current		-	1.6		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics curves

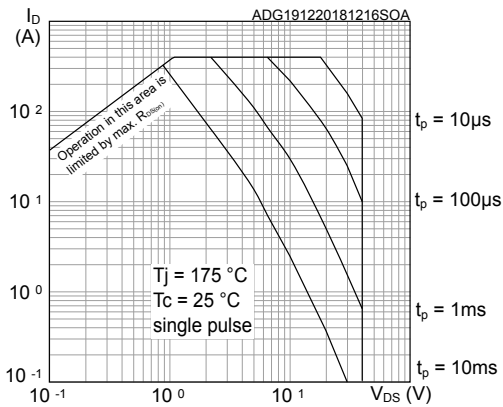
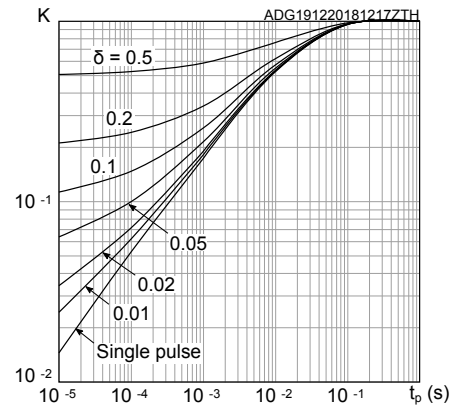
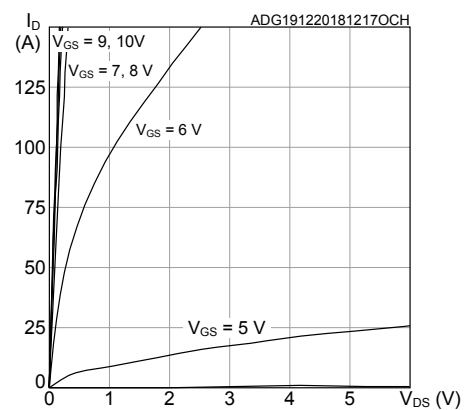
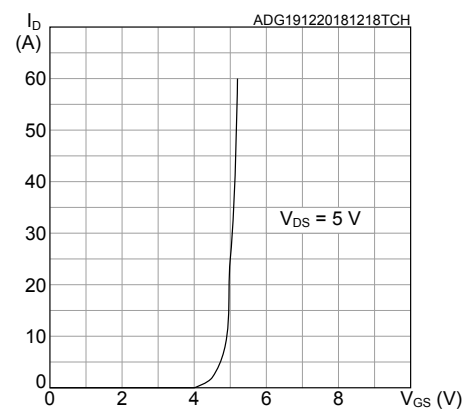
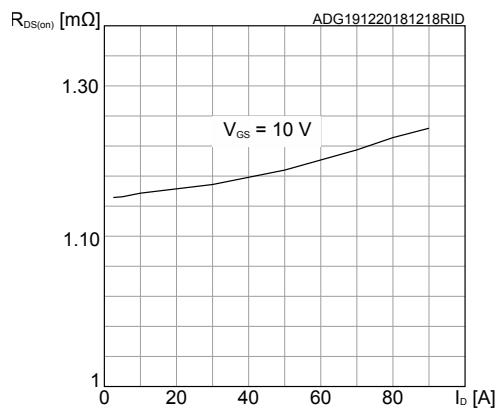
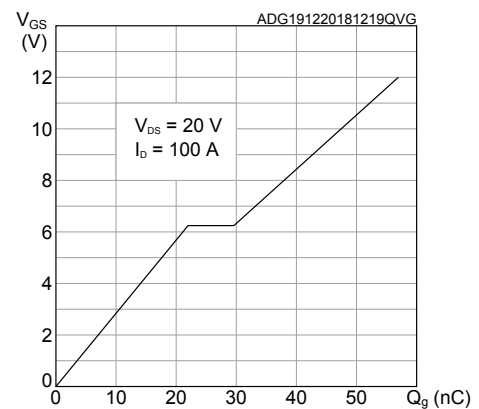
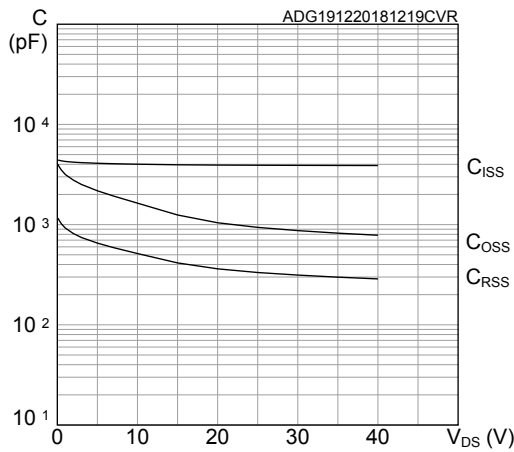
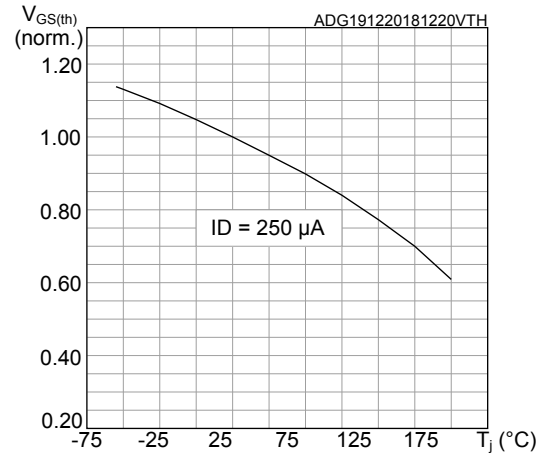
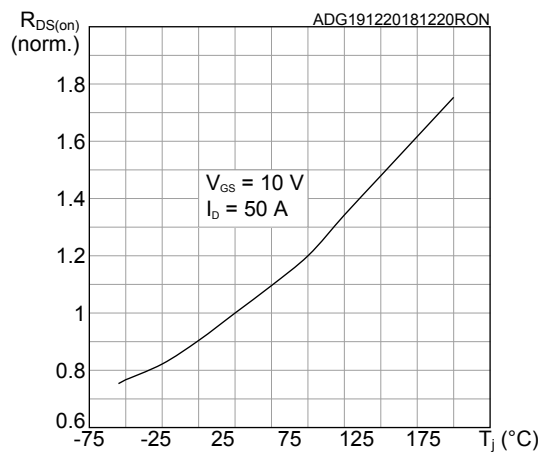
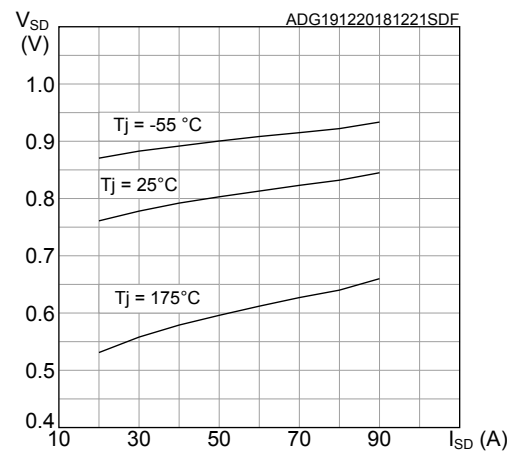
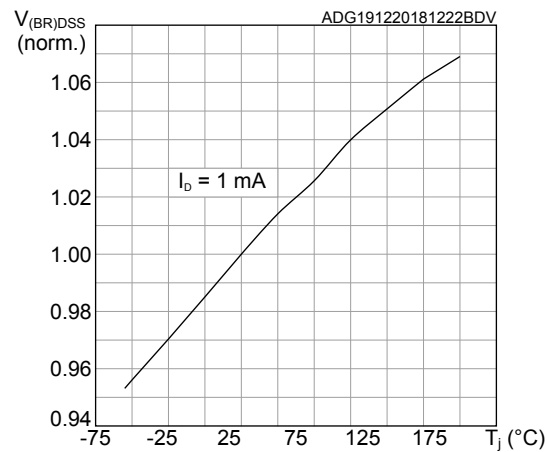
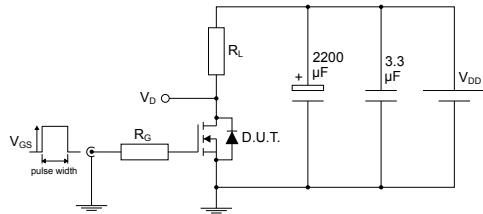
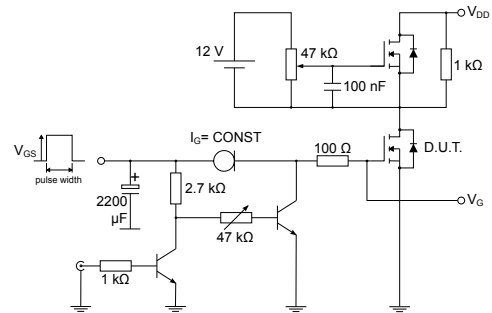
Figure 1. Safe operating area

Figure 2. Thermal impedance

Figure 3. Output characteristics

Figure 4. Transfer characteristics

Figure 5. Static drain-source on resistance

Figure 6. Gate charge vs gate-source voltage


Figure 7. Capacitance variations

Figure 8. Normalized gate threshold voltage vs temperature

Figure 9. Normalized on resistance vs temperature

Figure 10. Source-drain diode forward characteristic

Figure 11. Normalized $V_{(BR)DSS}$ vs temperature


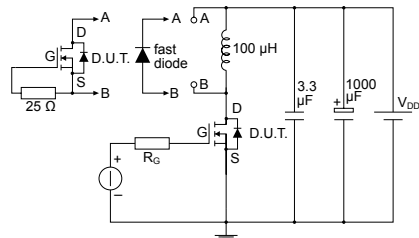
3 Test circuits

Figure 12. Test circuit for resistive load switching times


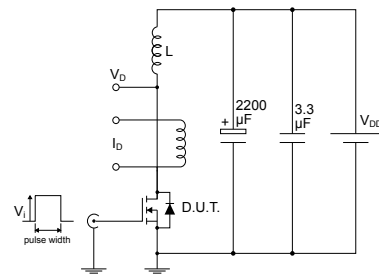
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Figure 13. Test circuit for gate charge behavior


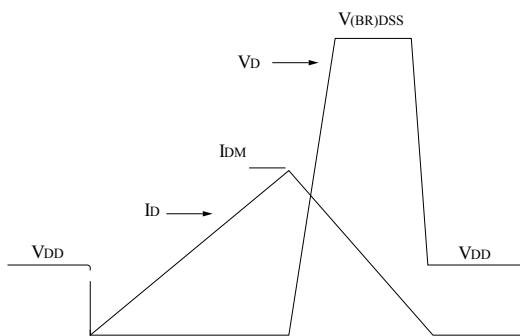
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Figure 14. Test circuit for inductive load switching and diode recovery times


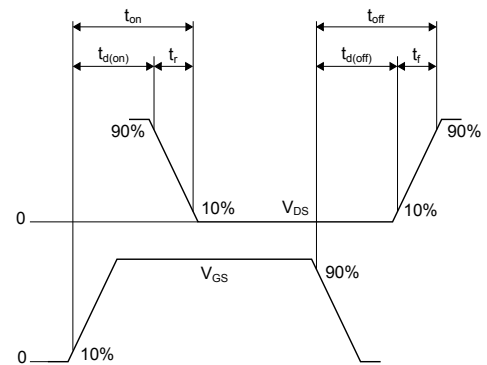
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Figure 15. Unclamped inductive load test circuit


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Figure 16. Unclamped inductive waveform


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Figure 17. Switching time waveform


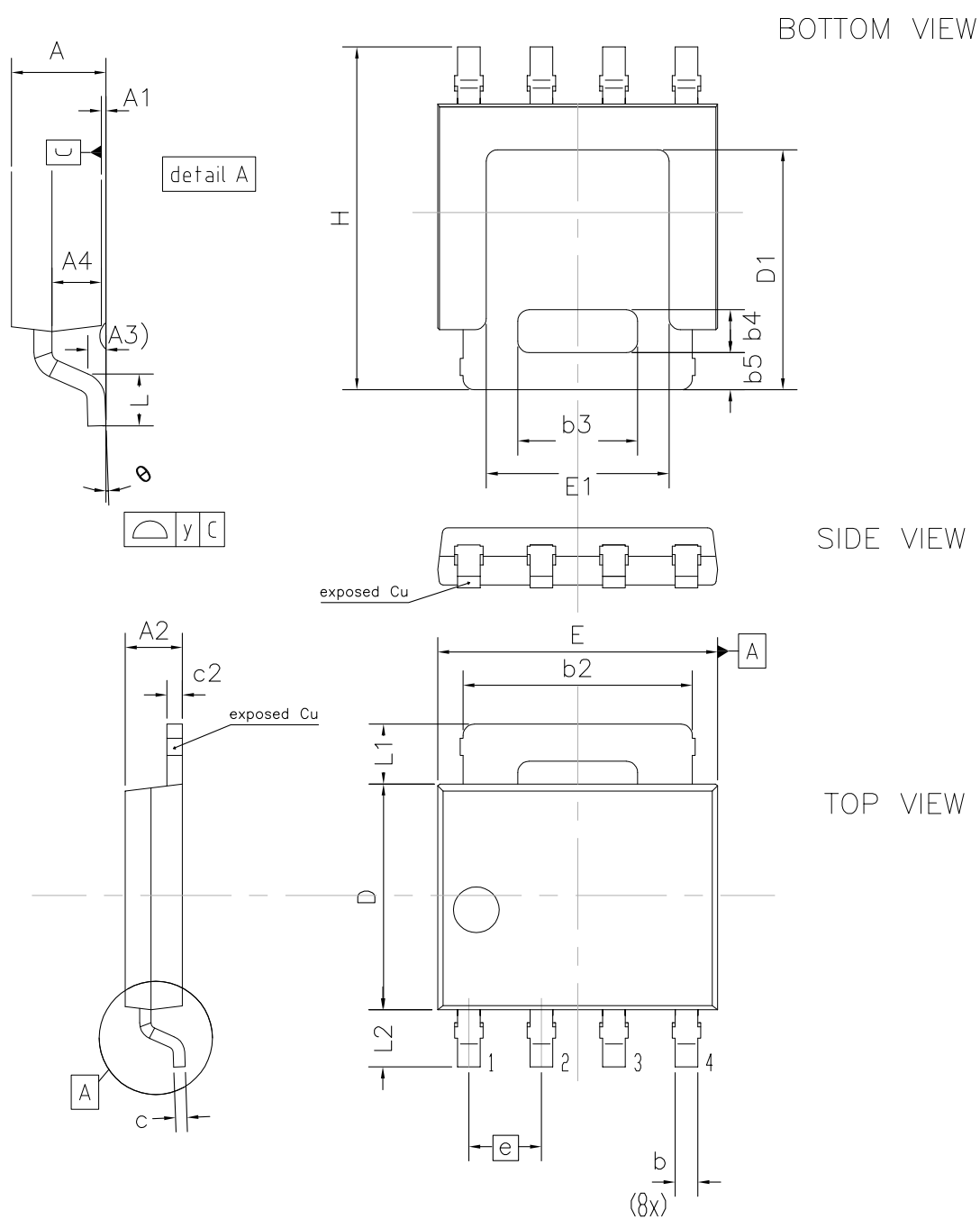
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 LFPK 5x6 package information

Figure 18. LFPAC 5x6 package outline



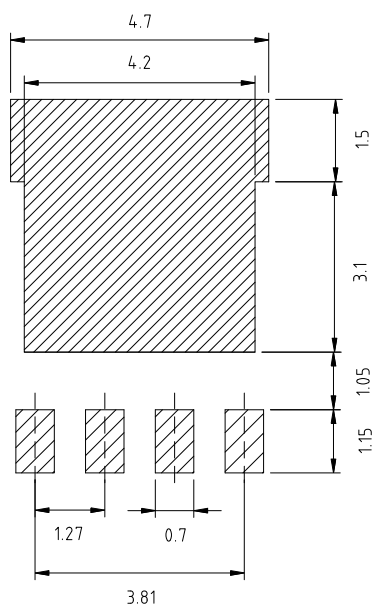
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Table 7. LFPACK 5x6 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	1.01		1.20
A1	0.00		0.15
A2	0.95		1.10
A3		0.25	
A4	0.50	0.55	0.65
b	0.35		0.50
b2	3.62		4.41
b3	2.0		2.20
b4	0.70		0.90
b5			0.7
c	0.19	0.20 ⁽¹⁾	0.25
c2	0.24		0.30
D	3.80		4.10
D1	3.80	4.00	4.20
E	4.8		5.0
E1	3.1		3.3
e		1.27	
H	5.8		6.2
L	0.40		0.85
L1	0.80		1.30
L2	0.80		1.3
w		0.25	
y		0.10	
Θ	0°		8°

1. Dimension without plating

Figure 19. LFPK 5x6 recommended footprint



00299525_FP_A

Revision history

Table 8. Document revision history

Date	Revision	Changes
09-Apr-2018	1	First release.
14-Jan-2019	2	Updated title in cover page, Section 1 Electrical ratings and Section 2 Electrical characteristics . Added Section 2.1 Electrical characteristics curves Minor text changes.

Contents

1	Electrical ratings	2
2	Electrical characteristics.....	3
2.1	Electrical characteristics curves	3
3	Test circuits	6
4	Package information.....	7
4.1	LFPACK 5x6 package information	7
	Revision history	11

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